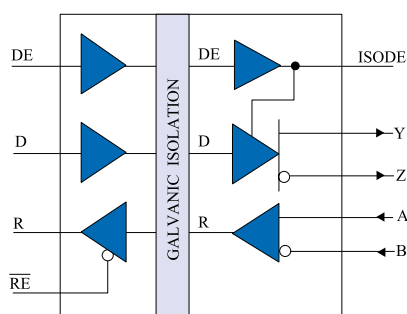


Isolated RS422/RS485 Interface

Functional Diagram



Function Table

V_{ID1} (Y-Z)	V_{ID2} (A-B)	DE	RE	ISODE	R	D	MODE
X	$\geq 0.2V$	X	L	X	H	X	Receive
X	$\leq -0.2V$	X	L	X	L	X	Receive
$-7 < V_{ID1} < 12$	$-7 < V_{ID2} < 12$	X	H	X	Z	X	Receive/Drive
≥ 1.5	X	H	L	H	H	H	Drive
≤ -1.5	X	H	L	H	L	L	Drive
	Open	L	L	L	H	X	Receive

H= High Level, L= Low Level,
X= Irrelevant, Z= High Impedance

Ordering Information

Order as IL422. If requesting tape and reel, please specify as IL422TR.

Features

- 2500 V_{RMS} Isolation (1 min)
- 25 ns Propagation Delay
- 25 MBaud Data Rate
- 1 ns Pulse Skew (typ)
- ± 60 mA Driver Output Capability
- Thermal Shutdown Protection
- Meets or Exceeds EIA 422-B, EIA 485-A and ITU Recommendation V11
- $-40^{\circ}C$ to $+85^{\circ}C$ Temperature Range
- 16 Pin SOIC Package
- PROFIBUS International Component Recognition
- UL 1577 Approval (pending)
- IEC 61010-1 Approval (pending)



Applications

Multi-point or Multi-drop Transmission on Long Bus Lines in Noisy Environments

Description

The IL422 is a galvanically isolated, high speed differential driver and receiver pair, designed for bidirectional data communication on balanced transmission lines. Isolation is achieved through patented* IsoLoop® technology. The IL422 is the first isolated RS-422 interface available in a standard 16 pin SOIC package, which meets the ANSI Standards EIA/TIA-422-B and RS485.

The IL422 has current limiting and thermal shutdown features to protect against output short circuits and bus contention situations where these may cause excessive power dissipation.

IsoLoop® is a registered trademark of NVE Corporation

* US Patent number 5,831,426; 6,300,617 and others

IL422^{IsoLoop®}

Absolute Maximum Ratings

Parameters	Symbol	Min.	Max.	Units
Storage Temperature	T _S	-65	150	°C
Ambient Operating Temperature	T _A	-40	85	°C
Voltage Range at A or B Bus Pins		-7	12	V
Supply Voltage ⁽¹⁾	V _{DD1} , V _{DD2}	-0.5	7	V
Digital Input Voltage		-0.5	5.5	V
Digital Output Voltage		-0.5	V _{DD} + 0.1	V
Continuous Total Power Dissipation			725 377	mW (25°C) mW (85°C)
Maximum Output Current	I _O		95	mA
Lead Solder Temperature (10s)			260	°C
ESD	2kV Human Body Model			

Insulation Specifications

Parameter	Condition	Min.	Typ.	Max.	Units
Creepage Distance (External)		8.077			mm
Barrier Impedance			>10 ¹⁴ 7		Ω pF
Leakage Current	240 V _{RMS} 60Hz		0.2		μA

Recommended Operating Conditions

Parameters	Symbol	Min.	Max.	Units
Supply Voltage	V _{DD1} , V _{DD2}	4.5	5.5	V
Input Voltage at any bus terminal (separately or common mode)	V _I V _{IC}		12 -7	V
High-level Digital Input Voltage	V _{IH}	3.0		V
Low-Level Digital Input Voltage	V _{IL}		0.8	V
Differential Input Voltage ⁽²⁾	V _{ID}		±12	V
High-Level Output Current (Driver)	I _{OH}		-60	mA
High-Level Digital Output Current (Receiver)	I _{OH}		8	mA
Low-Level Output Current (Driver)	I _{OL}		60	mA
Low-Level Digital Output Current (Receiver)	I _{OL}		8	mA
Operating Free Air Temperature	T _A	-40	85	°C
Digital Input Signal Rise and Fall Times	t _{IR} , t _{IF}	DC Stable		

IEC61010-1

TUV Certificate Numbers: *Pending*

Classification as Table 1.

Model	Pollution Degree	Material Group	Max Working Voltage	Package Type
IL422	II	III	400 V _{RMS}	16-SOIC (0.3")

UL 1577

Component Recognition program. File # *Pending*

Rated 2500Vrms for 1min.

Driver Section

All Specifications are T_{min} to T_{max} unless otherwise stated.

Parameter	Symbol	Min.	Typ. ⁽⁵⁾	Max.	Units	Test Conditions
Input Clamp Voltage	V _{IK}			-1.5	V	I _L =-18mA
Output Voltage	V _O	0		6	V	I _O =0
Differential Output Voltage	V _{OD1}	1.5		6	V	I _O =0
Differential Output Voltage ⁽⁶⁾	V _{OD2}	1.5	2.5	5	V	R _L =54Ω
Differential Output Voltage	V _{OD3}	1.5		5	V	V _{test} =-7 to 12V
Change in Magnitude of ⁽⁷⁾ Differential Output Voltage	Δ V _{OD}			±0.2	V	R _L =54 or 100Ω
Common Mode Output Voltage	V _{OC}			3 -1	V	R _L =54 or 100Ω
Change in Magnitude of ⁽⁷⁾ Common Mode Output Voltage	Δ V _{OC}			±0.2	V	R _L =54 or 100Ω
Output Current ⁽⁴⁾	I _O			1 -0.8	mA mA	Output Disabled V _O =12 V _O =-7
High Level Input Current	I _{IH}			10	μA	V _I =3.5 V
Low Level Input Current	I _{IL}			-10	μA	V _I =0.4 V
Short-Circuit Output Current	I _{OS}			-250 -150 250	mA	V _O = -6 V _O = 0 V _O = 8
Supply Current (V _{DD2} = +5V) (V _{DD1} = +5V)	I _{DD2} I _{DD1}		27 5	34 10	mA mA	No Load (Outputs Enabled)
Switching Characteristics						
Parameter	Symbol	Min.	Typ. ⁽⁵⁾	Max.	Units	Test Conditions
Maximum Data Rate		25			Mbd	R _L =54Ω, C _L =50pF
Differential Output Delay Time	t _{D(OD)}		16	25	ns	R _L =54Ω, C _L =50pF
Pulse Skew ⁽¹⁰⁾	t _{SK(P)}		1	6	ns	R _L =54Ω, C _L =50pF
Differential Output Transition Time	t _{T(OD)}		8	10	ns	R _L =54Ω, C _L =50pF
Output Enable Time To High Level	t _{PZH}		31	65	ns	R _L =54Ω, C _L =50pF
Output Enable Time To Low Level	t _{PZL}		22	35	ns	R _L =54Ω, C _L =50pF
Output Disable Time From High Level	t _{PHZ}		28	50	ns	R _L =54Ω, C _L =50pF
Output Disable Time From Low Level	t _{PLZ}		16	32	ns	R _L =54Ω, C _L =50pF
Skew Limit ⁽³⁾	t _{SK(LIM)}		2	8	ns	R _L =54Ω, C _L =50pF

IL422 IsoLoop®

Receiver Section

All Specifications are T_{min} to T_{max} unless otherwise stated.

Parameter	Symbol	Min.	Typ. ⁽⁵⁾	Max.	Units	Test Conditions
Positive-going Input Threshold Voltage	V _{IT+}			0.2	V	V _O = 2.7V, I _O = - 0.4mA
Negative-going Input Threshold Voltage	V _{IT-}	-0.2			V	V _O = 0.5V, I _O = 8mA
Hysteresis Voltage (V _{IT+} - V _{IT-})	V _{hys}		60		mV	
High Level Digital Output Voltage	V _{OH}	V _{DD} - 0.1			V	V _{ID} = 200mV, I _{OH} = -20μA
Low Level Digital Output Voltage	V _{OL}			0.2	V	V _{ID} = -200mV, I _{OL} = 20μA
High-impedance-state output current	I _{OZ}			±10	μA	V _O = 0.4 to (V _{DD2} - 0.5) V
Line Input Current ⁽⁸⁾	I _I			1 -0.8	mA	Other Input ⁽¹⁾ = 0V V _I = 12V V _I = -7V
Input Resistance	r _I		50		kΩ	
Supply Current (V _{DD2} = +5) (V _{DD1} = +5)	I _{DD2} I _{DD1}		27 5	34 10	mA mA	No Load (Outputs Enabled)
Switching Characteristics						
Parameter	Symbol	Min.	Typ. ⁽⁵⁾	Max.	Units	Test Conditions
Maximum Data Rate		25			Mbd	R _L = 54Ω, C _L = 50pF
Propagation Time ⁽⁹⁾	t _{PD}		24	32	ns	V _O = -1.5 to 1.5V, C _L = 15pF
Pulse Skew ⁽¹⁰⁾	t _{SK(P)}		1	6	ns	V _O = -1.5 to 1.5V, C _L = 15pF
Skew Limit ⁽³⁾	t _{SK(lim)}		2	8	ns	R _L = 54Ω, C _L = 50pF
Output Enable Time To High Level	t _{PZH}		17	24	ns	C _L = 15pF
Output Enable Time To Low Level	t _{PZL}		30	45	ns	C _L = 15pF
Output Disable Time From High Level	t _{PHZ}		30	45	ns	C _L = 15pF
Output Disable Time From Low Level	t _{PLZ}		18	27	ns	C _L = 15pF

Electrostatic Discharge Sensitivity

This product has been tested for electrostatic sensitivity to the limits stated in the specifications. However, NVE recommends that all integrated circuits be handled with appropriate care to avoid damage. Damage caused by inappropriate handling or storage could range from performance degradation to complete failure.

Notes:

1. All Voltage values are with respect to network ground except differential I/O bus voltages.
2. Differential input/output voltage is measured at the noninverting terminal A/Y with respect to the inverting terminal B/Z.
3. Skew limit is the maximum difference in any two channels in one device.
4. The power-off measurement in ANSI Standard EIA/TIA-422-B applies to disabled outputs only and is not applied to combined inputs and outputs.
5. All typical values are at $V_{DD1}, V_{DD2} = 5V$ and $T_A = 25^\circ C$.
6. The minimum V_{OD2} with a 100Ω load is either $\frac{1}{2}V_{OD1}$ or 2V, whichever is greater.
7. $\Delta|V_{OD}|$ and $\Delta|V_{OC}|$ are the changes in magnitude of V_{OD} and V_{OC} , respectively, that occur when the input is changed from one logic state to the other.
8. This applies for both power on and power off, refer to ANSI standard RS-485 for exact condition. The EIA/TIA-422-B limit does not apply for a combined driver and receiver terminal.
9. Includes 8 ns read enable time. Maximum propagation delay is 25 ns after read assertion.
10. Pulse skew is defined as the $|t_{PLH} - t_{PHL}|$ of each channel.

Application Notes:

Power Consumption

IsoLoop® devices achieve their low power consumption from the manner by which they transmit data across the isolation barrier. By detecting the edge transitions of the input logic signal and converting these to narrow current pulses a magnetic field is created around the GMR Wheatstone bridge. Depending on the direction of the magnetic field, the bridge causes the output comparator to switch following the input logic signal. Since the current pulses are narrow, about 2.5ns wide, the power consumption is independent of mark-to-space ratio and solely dependent on frequency. This has obvious advantages over optocouplers whose power consumption is heavily dependent on its on-state and frequency.

The approximate power supply current per channel for

$$\text{IsoLoop}^\circ \text{ is: } I(\text{input}) = 40 \left(\frac{f}{f_{\max}} \right) \left(\frac{1}{4} \right) \text{ mA}$$

where f = operating frequency

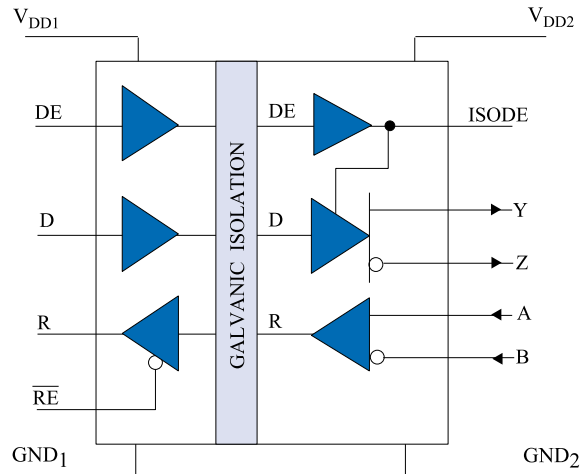
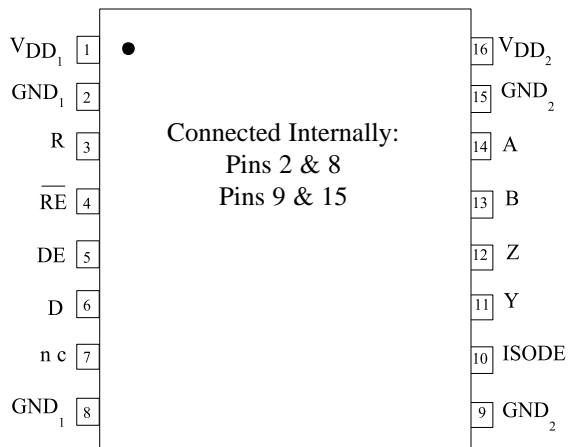
$f_{\max} = 50 \text{ MHz}$

Power Supplies

It is recommended that low ESR ceramic capacitors be used to decouple the supplies. Both V_{DD1} and V_{DD2} should be bypassed with 47 nF capacitors. These should be placed no further than 1 cm from the device pins for proper operation. In addition, V_{DD2} should have a 10 μF tantalum capacitor connected in parallel with the 47 nF capacitor.

IL422^{IsoLOOP®}

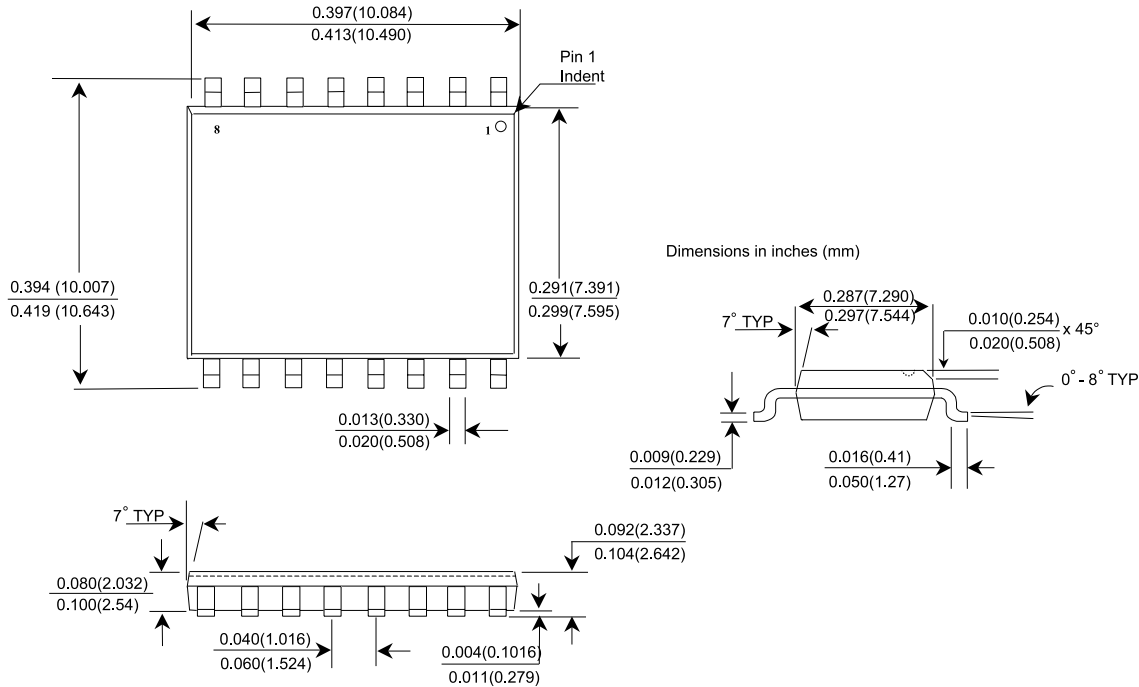
Pin Configuration



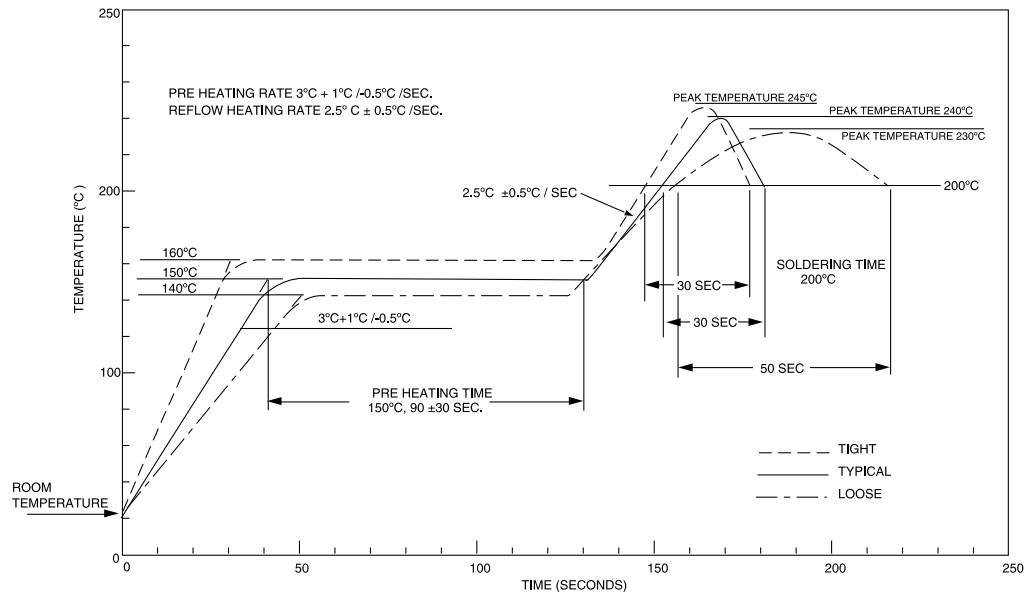
Pin Description


Pin	Mnemonic	Description
1	V _{DD1}	Input Power Supply
2	GND ₁	Input Power Supply Ground Return
3	R	Output Data from AB Bus
4	RE	Read Data Enable (If RE is high, R is High Impedence)
5	DE	Drive Enable
6	D	Data Input to YZ Bus
7	nc	No Internal Connection
8	GND ₁	Input Power Supply Ground Return
9	GND ₂	Output Power Supply Ground Return
10	ISODE	Isolated DE Output for use in applications where the state of the drive enable node needs to be monitored
11	Y	'Y' Bus (Drive — True)
12	Z	'Z' Bus (Drive — Inverse)
13	B	'B' Bus (Receive — Inverse)
14	A	'A' Bus (Receive — True)
15	GND ₂	Output Power Supply Return
16	V _{DD2}	Output Power Supply

0.3" SOIC-16 Package



IR Soldering Profile





About NVE

An ISO 9001 Certified Company

NVE Corporation is a high technology components manufacturer having the unique capability to combine leading edge Giant Magnetoresistive (GMR) materials with integrated circuits to make high performance electronic components. Products include Magnetic Field Sensors, Magnetic Field Gradient Sensors (Gradiometer), Digital Magnetic Field Sensors, Digital Signal Isolators and Isolated Bus Transceivers.

NVE is a leader in GMR research and in 1994 introduced the world's first products using GMR material, a line of GMR magnetic field sensors that can be used for position, magnetic media, wheel speed and current sensing.

NVE is located in Eden Prairie, Minnesota, a suburb of Minneapolis. Please visit our Web site at www.nve.com or call 952-829-9217 for information on products, sales or distribution.

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Specifications shown are subject to change without notice.

ISB-DS-001-IL422-D
February 2002

